

2SK2570

Silicon N-Channel MOS FET
Low Frequency Power Switching

HITACHI

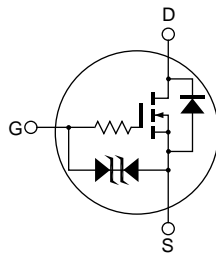
ADE-208-574
1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 0.8\Omega$ typ. ($V_{GS} = 4\text{ V}$, $I_D = 100\text{ mA}$)
- 2.5V gate drive devices.
- Small package (MPAK)

Outline

MPAK



1. Source
2. Gate
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	20	V
Gate to source voltage	V_{GSS}	±10	V
Drain current	I_D	0.2	A
Drain peak current	$I_{D(pulse)}^{*1}$	0.4	A
Channel dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

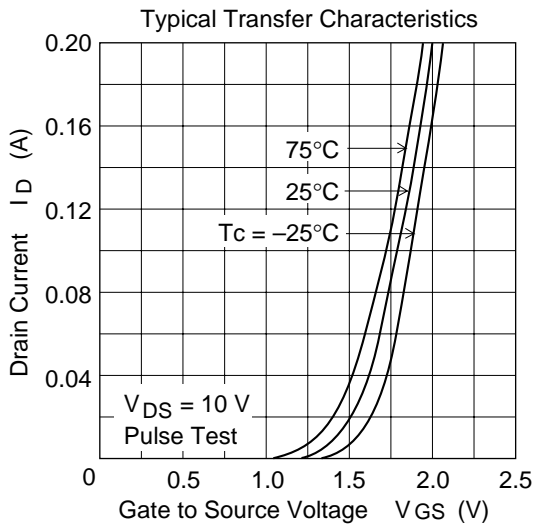
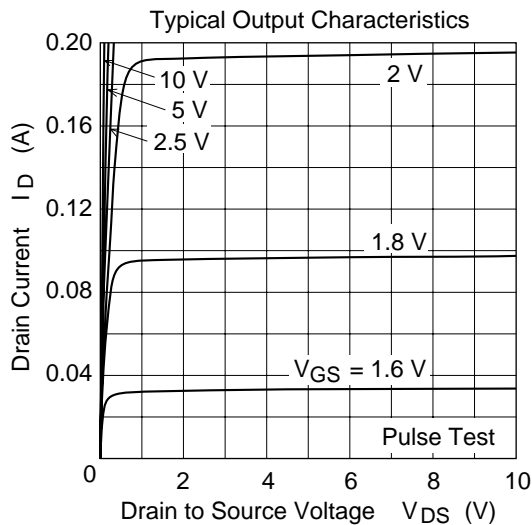
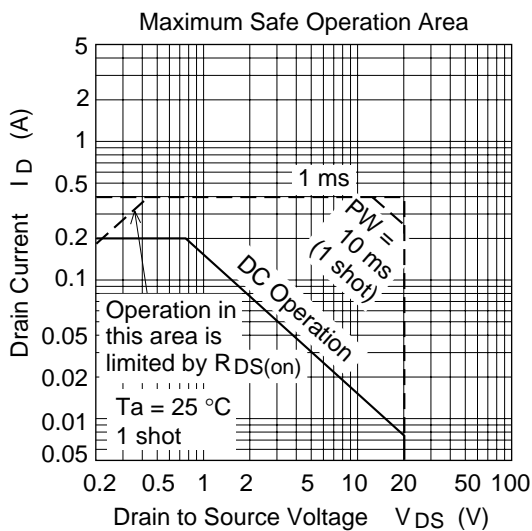
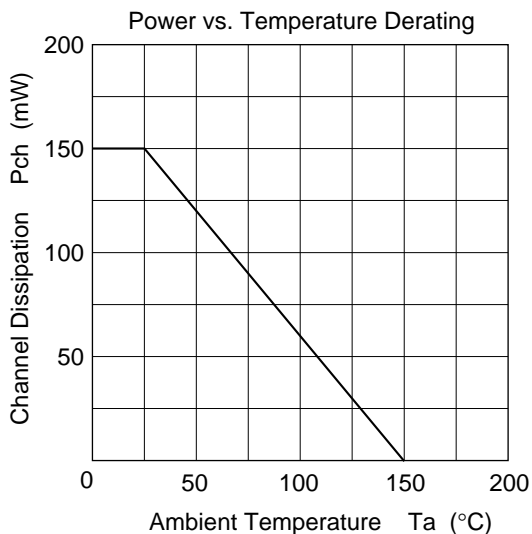
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	20	—	—	V	$I_D = 10\mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±10	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 20 V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±5.0	μA	$V_{GS} = \pm 6.5V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	—	1.5	V	$I_D = 10\mu A, V_{DS} = 5V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.8	1.1	Ω	$I_D = 100 mA$ $V_{GS} = 4V^{*1}$
		—	1.3	2.2	Ω	$I_D = 40 mA$ $V_{GS} = 2.5V^{*1}$
Forward transfer admittance	$ y_{fs} $	0.22	0.35	—	S	$I_D = 100 mA$ $V_{DS} = 10V^{*1}$
Input capacitance	Ciss	—	45	—	pF	$V_{DS} = 10V$
Output capacitance	Coss	—	33	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	9.6	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{GS} = 5V, I_D = 100 mA$
Rise time	t_r	—	60	—	ns	$R_L = 100\Omega$
Turn-off delay time	$t_{d(off)}$	—	240	—	ns	
Fall time	t_f	—	140	—	ns	

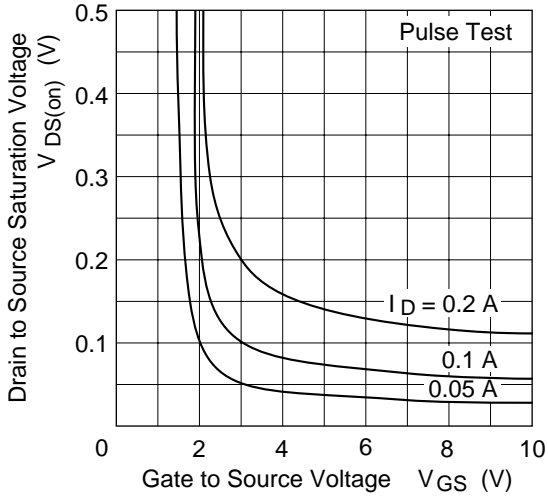
Notes: 1. Pulse test

2. Marking is "ZL—"

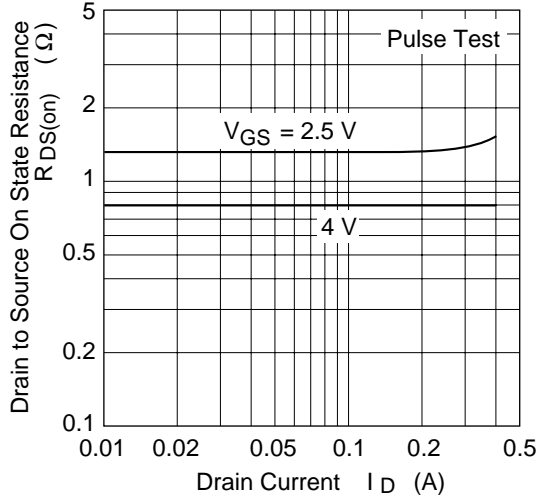
Main Characteristics



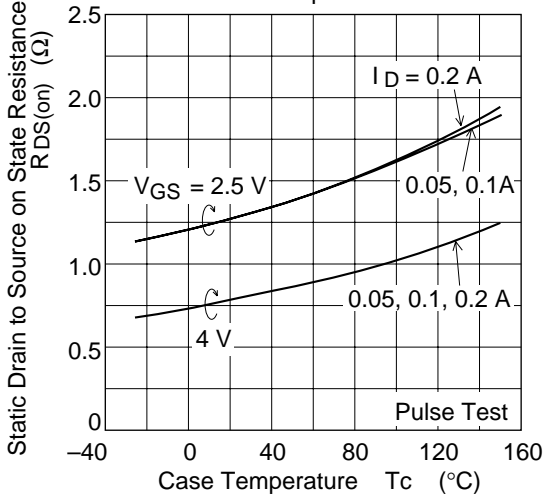
Drain to Source Saturation Voltage vs. Gate to Source Voltage



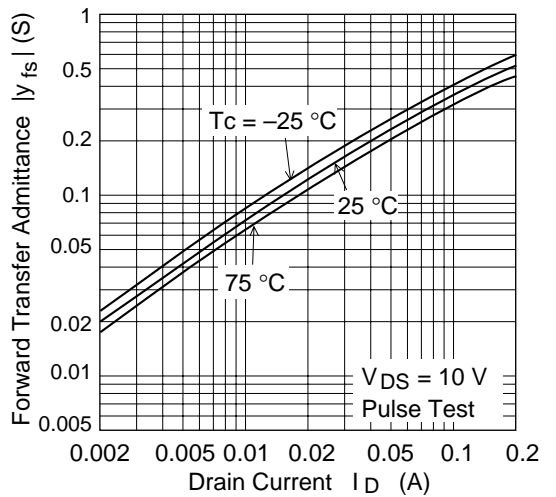
Static Drain to Source on State Resistance vs. Drain Current



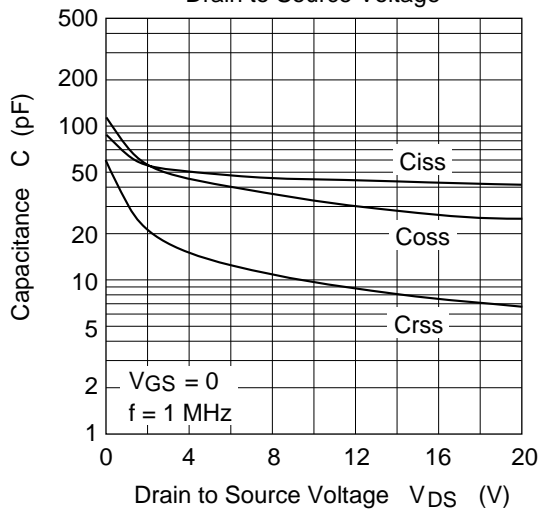
Static Drain to Source on State Resistance vs. Temperature



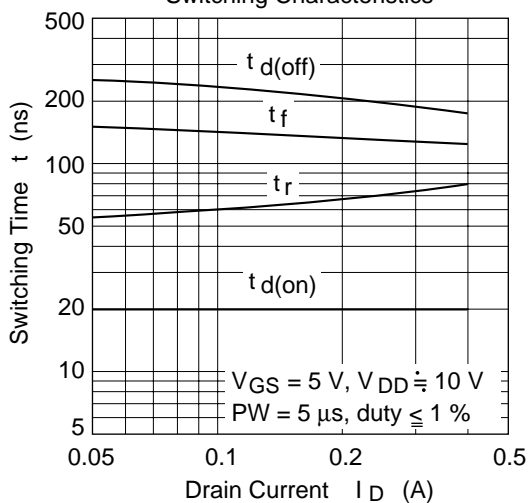
Forward Transfer Admittance vs. Drain Current



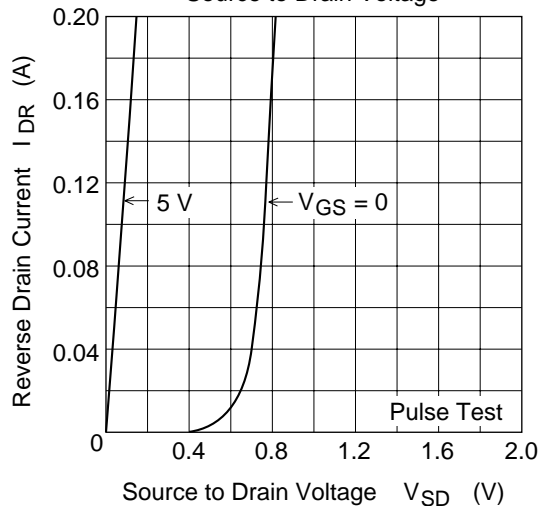
Typical Capacitance vs. Drain to Source Voltage



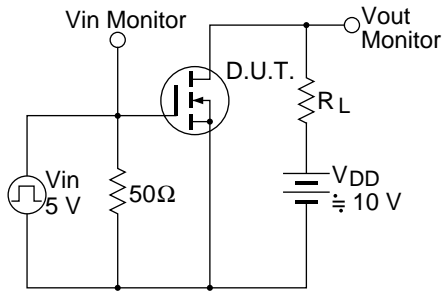
Switching Characteristics



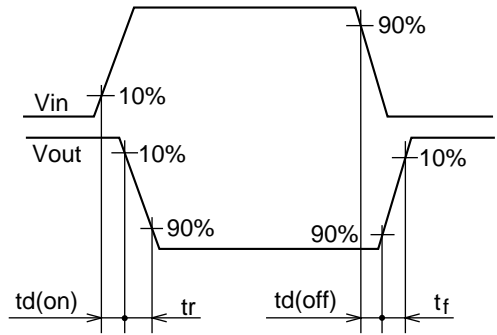
Reverse Drain Current vs. Source to Drain Voltage



Switching Time Test Circuit

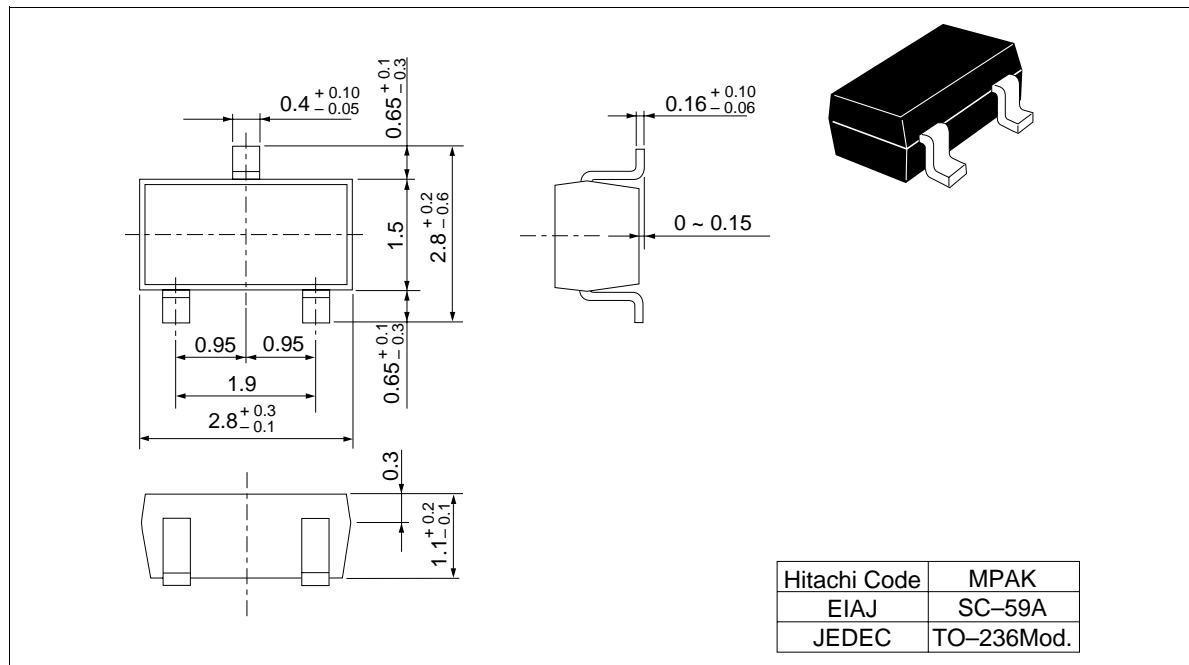


Waveform



Package Dimensions

Unit: mm



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